## Silicon Switching Diode

- For high-speed switching applications
- Pb-free (RoHS compliant) package ${ }^{1)}$
- Qualified according AEC Q101



## BAL99



| Type | Package | Configuration | Marking |
| :--- | :--- | :--- | :--- |
| BAL99 | SOT23 | single | JFs |

Maximum Ratings at $T_{\mathrm{A}}=25^{\circ} \mathrm{C}$, unless otherwise specified

| Parameter | Symbol | Value | Unit |
| :--- | :--- | :---: | :--- |
| Diode reverse voltage | $V_{\mathrm{R}}$ | 80 | V |
| Peak reverse voltage- | $V_{\mathrm{RM}}$ | 85 |  |
| Forward current | $\mathrm{F}_{\mathrm{F}}$ | 250 | mA |
| Peak forward current | $\mathrm{I}_{\mathrm{FM}}$ | - |  |
| Surge forward current, $t=1 \mu \mathrm{~s}$ | F $_{\mathrm{SS}}$ | 4.5 | A |
| Total power dissipation <br> $T_{\mathrm{S}} \leq 54^{\circ} \mathrm{C}$ | $P_{\mathrm{tot}}$ | 370 | mW |
| Junction temperature | $T_{\mathrm{J}}$ |  |  |
| Storage temperature | $T_{\text {stg }}$ | $-65 \ldots 150$ |  |

## Thermal Resistance

| Parameter | Symbol | Value | Unit |
| :--- | :--- | :---: | :--- |
| Junction - soldering point ${ }^{2}$ ) | $R_{\text {thJS }}$ | $\leq 260$ | K/W |

[^0]Electrical Characteristics at $T_{\mathrm{A}}=25^{\circ} \mathrm{C}$, unless otherwise specified

| Parameter | Symbol | Values |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
|  |  | min. | typ. | max. |  |
| DC Characteristics |  |  |  |  |  |
| Breakdown voltage $l_{(\mathrm{BR})}=100 \mu \mathrm{~A}$ | $V(\mathrm{BR})$ | 85 | - | - | V |
| Reverse current $\begin{aligned} & V_{\mathrm{R}}=70 \mathrm{~V} \\ & V_{\mathrm{R}}=25 \mathrm{~V}, T_{\mathrm{A}}=150^{\circ} \mathrm{C} \\ & V_{\mathrm{R}}=70 \mathrm{~V}, T_{\mathrm{A}}=150^{\circ} \mathrm{C} \end{aligned}$ | /R |  | - - - | $\begin{gathered} 1 \\ 30 \\ 50 \end{gathered}$ | $\mu \mathrm{A}$ |
| Forward voltage $\begin{aligned} & I_{F}=1 \mathrm{~mA} \\ & I_{F}=10 \mathrm{~mA} \\ & I_{F}=50 \mathrm{~mA} \\ & I_{F}=150 \mathrm{~mA} \end{aligned}$ | $V_{F}$ | - - - - | - - - - | $\begin{gathered} 715 \\ 855 \\ 1000 \\ 1250 \end{gathered}$ | mV |

## AC Characteristics

| Diode capacitance <br> $V_{\mathrm{R}}=0 \mathrm{~V}, f=1 \mathrm{MHz}$ | $C_{\mathrm{T}}$ | - | - | 1.5 | pF |
| :--- | :--- | :--- | :--- | :--- | :--- |
| Reverse recovery time |  |  |  |  |  |
| $I_{\mathrm{F}}=10 \mathrm{~mA}, I_{\mathrm{R}}=10 \mathrm{~mA}$, measured at $I_{\mathrm{R}}=1 \mathrm{~mA}$, |  | $t_{\mathrm{rr}}$ | - | - | 4 |
| $R_{\mathrm{L}}=100 \Omega$ |  |  |  |  |  |

Test circuit for reverse recovery time


Puls generator: $t_{\mathrm{p}}=100 \mathrm{~ns}, D=0.05$,

$$
t_{\mathrm{r}}=0.6 \mathrm{~ns}, R_{\mathrm{i}}=50 \Omega
$$

Oscillograph: $R=50, t_{\mathrm{r}}=0.35 \mathrm{~ns}$

$$
C \leq 1 \mathrm{pf}
$$

Reverse current $/_{\mathrm{R}}=f\left(T_{\mathrm{A}}\right)$
$V_{\mathrm{R}}=$ Parameter


Forward current $I_{F}=f\left(V_{F}\right)$


Forward Voltage $V_{\mathrm{F}}=f\left(T_{\mathrm{A}}\right)$
IF = Parameter


Peak forward current $/_{\text {FM }}=f\left(t_{p}\right)$
$T_{\mathrm{A}}=25^{\circ} \mathrm{C}$


Forward current $I_{\mathrm{F}}=f\left(T_{\mathrm{S}}\right)$


Package Outline


1) Lead width can be 0.6 max. in dambar area

Foot Print


Marking Layout (Example)


Standard Packing
Reel $\varnothing 180 \mathrm{~mm}=3.000$ Pieces/Reel
Reel $\varnothing 330 \mathrm{~mm}=10.000$ Pieces/Reel


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[^0]:    ${ }^{1} \mathrm{~Pb}$-containing package may be available upon special request
    ${ }^{2}$ For calculation of $R_{\mathrm{th} J A}$ please refer to Application Note Thermal Resistance

